


150nm \updownarrow

SiN

Si

$500\mu\text{m}$



The diagram shows a cross-section of a device. It consists of a dark grey substrate labeled 'Si' and a blue layer on top labeled 'SiN'. The SiN layer has a thickness of 150 nm, indicated by a vertical double-headed arrow on the left. A horizontal double-headed arrow in the center indicates a length of 500 micrometers. The SiN layer is wider than the Si substrate, forming a trapezoidal shape on both sides. The central part of the Si substrate is exposed, forming a channel of 500 micrometers in length.